

Silicon NPN Power Transistors

2SD1439

DESCRIPTION

- With TO-3PN package
- Built-in damper diode
- High voltage ,high reliability
- High speed switching
- Wide area of safe operation

APPLICATIONS

- For horizontal deflection output applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

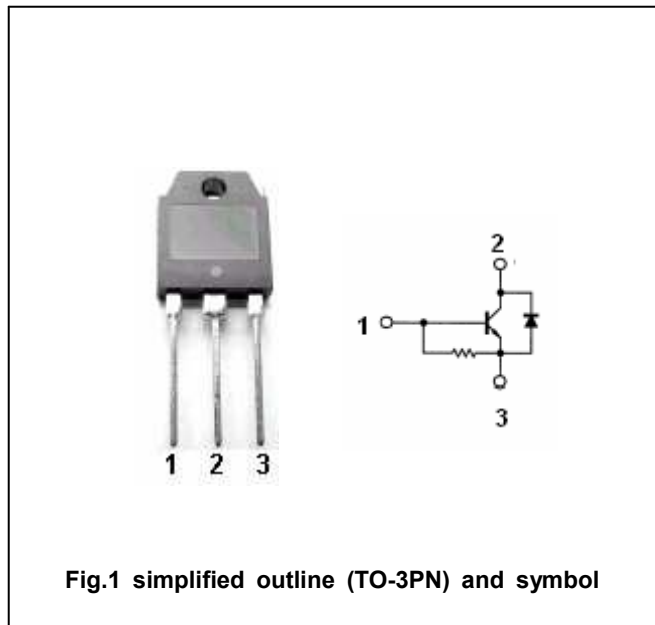


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current (DC)		3	A
I_{CM}	Collector current (Pulse)		10	A
I_{BM}	Base current (Pulse)		3.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	50	W
T_j	Junction temperature		130	°C
T_{stg}	Storage temperature		-55~130	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =500mA; I _C =0	5			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =2A; I _B =0.75A			5.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =2A; I _B =0.75A			1.5	V
I _{CB0}	Collector cut-off current	V _{CB} =750V; I _E =0			50	μA
I _{CB0}	Collector cut-off current	V _{CB} =1500V; I _E =0			1	mA
h _{FE}	DC current gain	I _C =2A; V _{CE} =10V	4		12	
t _s	Storage time	I _C =2A I _{Bend} =0.75A, L _{Leak} =5μH			7.0	μs
t _f	Fall time				0.75	μs
V _F	Diode forward voltage	I _F =-4A, I _B =0			2.2	V

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PACKAGE OUTLINE

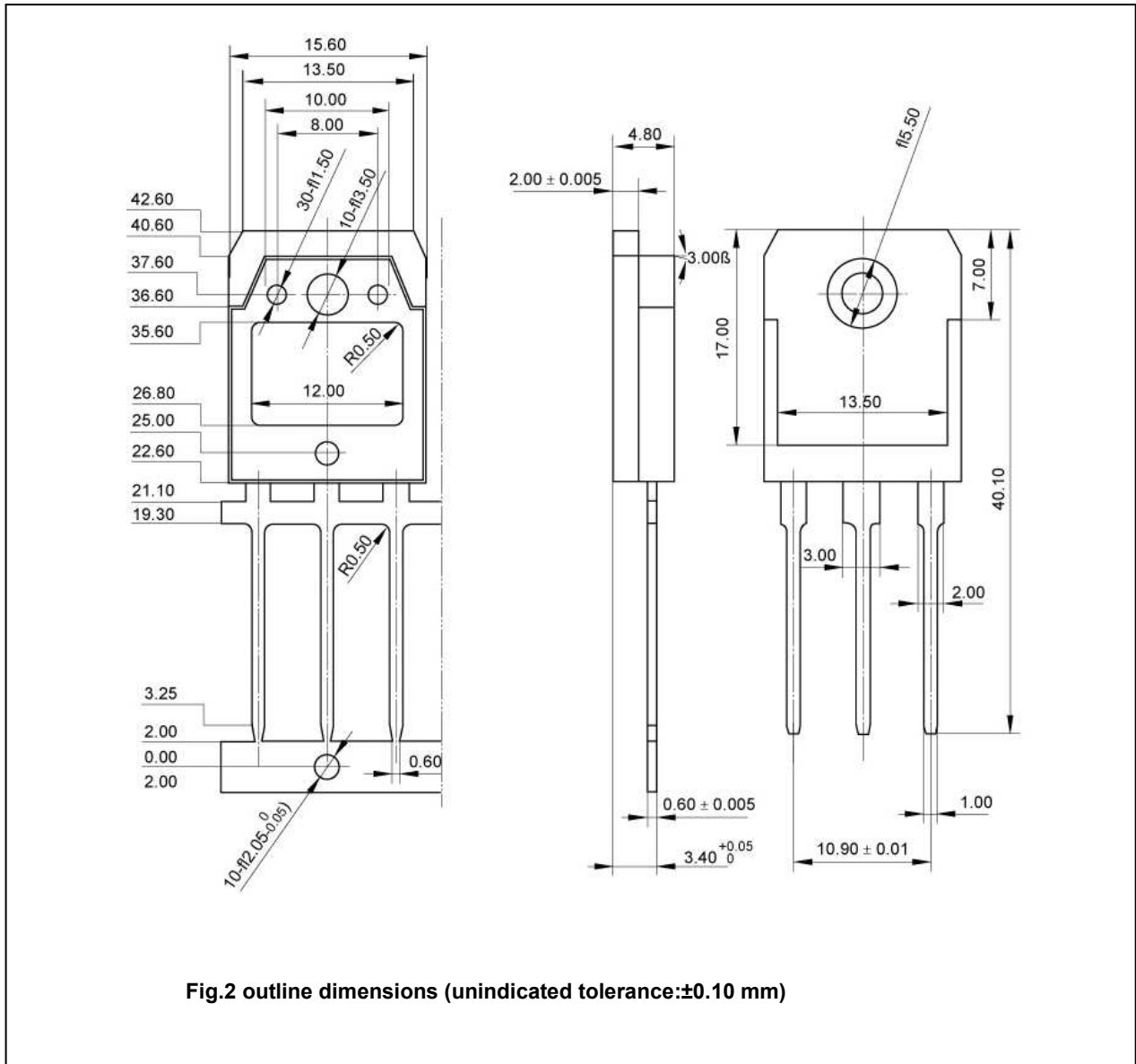


Fig.2 outline dimensions (unindicated tolerance: \pm 0.10 mm)

This datasheet has been downloaded from:

www.DatasheetCatalog.com

Datasheets for electronic components.